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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/607,274	06/27/2003	Satoshi Seo	60188-566	4710

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Jack Q. Lever, Jr.
McDERMOTT, WILL & EMERY
600 Thirteenth Street, N.W.
Washington, DC 20005-3096

EXAMINER

NGUYEN, KHIEM D

ART UNIT	PAPER NUMBER
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2823

DATE MAILED: 05/04/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/607,274

Applicant(s)

SATOSHI SEO

Examiner

Khiem D Nguyen

Art Unit

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☐ Responsive to communication(s) filed on ____.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-12 is/are pending in the application.
- 4a) Of the above claim(s) ____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) ____ is/are allowed.
- 6) ☒ Claim(s) 1-12 is/are rejected.
- 7) ☐ Claim(s) ____ is/are objected to.
- 8) ☐ Claim(s) ____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 27 June 2003 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on ____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. ____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892) 4) ☐ Interview Summary (PTO-413) Paper No(s). ____
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948) 5) ☐ Notice of Informal Patent Application (PTO-152)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 062703. 6) ☐ Other: ____

DETAILED ACTION

Drawings

Figures 20A to 21B should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). Additionally, the drawings are objected to because the scribe line regions are not clearly shown in the drawings. A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

1. Claims 1-5 are rejected under 35 U.S.C. 103(a) as being unpatentable over the applicant's admitted prior art (AAPA) of this application in view of Wakabayashi (U.S. Patent 6,607,970).

In re claim 1, AAPA discloses a method for fabricating a semiconductor device, the method comprising the steps of (Background of the invention, pages 1-2 and **FIGS. 20A-22**): (a) forming bonding pads (**FIG. 20A: 304**) above a wafer (**FIG. 20A: 302**) on which semiconductor elements (not shown) and an interconnect layer (not shown) are formed (page 1, lines 10-16); (b) forming a passivation film (**FIG. 20A: 306**) having apertures (**FIG. 20A: 306a and 306b**) including regions of the passivation film located

above parts of the bonding pads after the step (a) (page 1, lines 16-21); (c) forming a buffer coat film (**FIG. 20B: 308**) for covering part of the passivation film after the step (b); (d) forming, in the buffer coat film, apertures (**FIG. 20B: 308a**) including regions of the buffer coat film located above scribe line regions and above the parts of the bonding pads, respectively (page 1, line 22 to page 2, line 5); (e) bonding a surface protection tape (**FIG. 21A: 312**) to the wafer using an adhesive material (**FIG. 21A: 320**) after the step (d) (page 2, lines 2-5); and (f) polishing the rear surface of the wafer after the step (e) (**FIG. 21B: polishing slurry**) (page 2, lines 6-14).

AAPA does not explicitly disclose forming, in the buffer coat film, apertures including regions of the buffer coat film located above a periphery region having a certain distance from the periphery of the wafer, above scribe line regions and above the parts of the bonding pads, respectively.

Wakabayashi discloses a method for fabricating a semiconductor device, the method comprising the steps of: (a) forming bonding pads (**FIG. 7: 2**) above a wafer (**FIG. 7: 1**) on which semiconductor elements and an interconnect layer are formed (col. 3, lines 21-48); (b) forming a passivation film (**FIG. 7: 3**) having apertures (**FIG. 1: 4**) including regions of the passivation film located above parts of the bonding pads after the step (a) (col. 3, lines 37-48); (c) forming a buffer coat film for covering part of the passivation film after the step (b) (col. 3, lines 21-48); (d) forming, in the buffer coat film, apertures (**FIG. 7: 12**) including regions of the buffer coat film located above a periphery region having a certain distance from the periphery of the wafer, above scribe line regions (**FIG. 2: 7**) and above the parts of the bonding pads, respectively (col. 3,

lines 38-48); (e) bonding a surface protection tape (**FIG. 7: 14**) to the wafer using an adhesive material (**FIG. 7: 13**) after the step (d) (col. 3, line 64 to col. 4, line 27). It would have been obvious to one of ordinary skill in the art of making semiconductor devices to combine the teaching of AAPA and Wakabayashi to enable the process of forming, in the buffer coat film, apertures including regions of the buffer coat film located above a periphery region having a certain distance from the periphery of the wafer, above scribe line regions and above the parts of the bonding pads of AAPA to be performed and furthermore to prevent water or moisture from entering the interface between the insulating film 3 (protective film) and the seal film 13 and may oxidize the wirings 5 and the like. Moreover, a crack hardly develops in the interface between the insulation film 3 and the seal film 13 (col. 4, lines 36-43).

In re claim 2, Wakabayashi discloses wherein in the step (c), the buffer coat film is formed using a positive-type photosensitive material, and the step (d) includes a process for exposing part of the buffer coat film located on the periphery region of the wafer (col. 3, lines 38-48 and **FIG. 3**). Alternatively, AAPA disclose wherein the buffer coat film is formed using a positive-type photosensitive material (page 1, lines 22-24).

In re claim 3, Wakabayashi discloses wherein in the step (c), the buffer coat film is formed using a positive-type photosensitive material, and the step (d) includes a process for exposing part of the buffer coat film located on the wholes of chip regions at least partly overlapped with the periphery region of the wafer (col. 3, lines 38-48 and **FIG. 3**).

In re claim 4, AAPA and Wakabayashi disclose wherein in the step (c), the buffer coat film is formed using an organic resin, and the step (d) includes a process for selectively removing part of the buffer coat film located on the periphery region of the wafer by a solvent (AAPA, page 1, lines 22-24 and **FIGS. 21A-B**) Wakabayashi (col. 3, lines 38-48 and **FIG. 3**).

In re claim 5, AAPA and Wakabayashi discloses wherein in the step (c), the buffer coat film is formed using an organic resin, and the step (d) includes a process for blowing gas on part of the buffer coat film located on the periphery region of the wafer before the curing of the buffer coat film (AAPA, page 1, lines 22-24 and **FIGS. 21A-B**) Wakabayashi (col. 3, lines 38-48 and **FIG. 3**).

2. Claims 6-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over the applicant's admitted prior art (AAPA) of this application in view of Wakabayashi (U.S. Patent 6,607,970).

In re claims 6, 8, 9, 11, and 12, AAPA discloses a method for fabricating a semiconductor device, the method comprising the steps of (Background of the invention, pages 1-2 and **FIGS. 20A-22**): (a) forming bonding pads (**FIG. 20A: 304**) above a wafer (**FIG. 20A: 302**) on which semiconductor elements (not shown) and an interconnect layer (not shown) are formed (page 1, lines 10-16); (b) forming a passivation film (**FIG. 20A: 306**) having apertures (**FIG. 20A: 306a and 306b**) including regions of the passivation film located above parts of the bonding pads after the step (a) (page 1, lines 16-21); (c) forming a buffer coat film (**FIG. 20B: 308**) for covering part of the passivation film after the step (b); (d) forming, in the buffer coat film, apertures (**FIG.**

20B: 308a) including regions of the buffer coat film located above scribe line regions and above the parts of the bonding pads, respectively (page 1, line 22 to page 2, line 5); (e) bonding a surface protection tape (**FIG. 21A: 312**) to the wafer using an adhesive material (**FIG. 21A: 320**) after the step (d) (page 2, lines 2-5); and (f) polishing the rear surface of the wafer after the step (e) (**FIG. 21B: polishing slurry**) (page 2, lines 6-14).

AAPA does not explicitly disclose forming, in the buffer coat film, apertures including regions of the buffer coat film located above scribe line regions and above the parts of the bonding pads, respectively, and reducing the thickness of part of the buffer coat film located on a periphery region of the wafer having a certain distance from the periphery of the wafer.

Wakabayashi discloses a method for fabricating a semiconductor device, the method comprising the steps of: (a) forming bonding pads (**FIG. 7: 2**) above a wafer (**FIG. 7: 1**) on which semiconductor elements and an interconnect layer are formed (col. 3, lines 21-48); (b) forming a passivation film (**FIG. 7: 3**) having apertures (**FIG. 1: 4**) including regions of the passivation film located above parts of the bonding pads after the step (a) (col. 3, lines 37-48); (c) forming a buffer coat film for covering part of the passivation film after the step (b) (col. 3, lines 21-48); (d) forming, in the buffer coat film, apertures (**FIG. 7: 12**) including regions of the buffer coat film located above scribe line regions (**FIG. 2: 7**) and above the parts of the bonding pads with connection parts connecting between chip regions left among the apertures, respectively, and reducing the thickness of part of the buffer coat film located on a periphery region of the wafer having a certain distance from the periphery of the wafer (col. 3, lines 38-48); (e) bonding a

surface protection tape (**FIG. 7: 14**) to the wafer using an adhesive material (**FIG. 7: 13**) after the step (d) (col. 3, line 64 to col. 4, line 27). It would have been obvious to one of ordinary skill in the art of making semiconductor devices to combine the teaching of AAPA and Wakabayashi to enable the process of forming, in the buffer coat film, apertures including regions of the buffer coat film located above scribe line regions and above the parts of the bonding pads, respectively, and reducing the thickness of part of the buffer coat film located on a periphery region of the wafer having a certain distance from the periphery of the wafer of AAPA to be performed and furthermore to prevent water or moisture from entering the interface between the insulating film 3 (protective film) and the seal film 13 and may oxidize the wirings 5 and the like. Moreover, a crack hardly develops in the interface between the insulation film 3 and the seal film 13 (col. 4, lines 36-43).

In re claims 7-9, AAPA discloses wherein bonding a surface protection tape to the wafer using an adhesive paste having a thickness of 15 μm (page 2, lines 2-5) but does not explicitly disclose the thickness range as recited by the Applicants. However, there is no evidence indicating that the reducing thickness of part of the buffer coat film, the thickness of the adhesive paste, and the range of a viscosity of the polishing slurry is critical and it has been held that it is not inventive to discover the optimum or workable ranges of a result-effective variable within given prior art conditions by routine experimentation. See MPEP §2144.05. Note that the specification contains no disclosure of either the critical nature of the claimed dimensions of any unexpected results arising there from. Where patentability is aid to be based upon particular chosen dimensions or

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upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. In re Woodruff, 919 F.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

In re claim 10, AAPA discloses wherein the polishing slurry includes polyethylene glycol (page 2, lines 6-10).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Khiem D Nguyen whose telephone number is (571) 272-1865. The examiner can normally be reached on Monday-Friday (8:00 AM - 5:00 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on (571) 272-1855. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 305-3432 for regular communications and (703) 305-3432 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

K.N.
April 30, 2004

A handwritten signature in black ink, appearing to read 'W. David Coleman', with a horizontal line drawn underneath it.

**W. DAVID COLEMAN
PRIMARY EXAMINER**